

## Properties of Electrical Discharge Machinable SiC-TiB<sub>2</sub> Composites

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Electrical discharge machinable SiC-TiB<sub>2</sub> composites were fabricated by hot-pressing. Their mechanical and electrical properties were determined as a function of TiB<sub>2</sub> content. The addition of TiB<sub>2</sub> to SiC matrix increased the strength and toughness and decreased electrical resistivity. The flexural strength and fracture toughness of SiC-40 vol% TiB<sub>2</sub> composites were approximately 50% higher than those of monolithic SiC ceramics. Microstructural analysis showed that the toughening was mainly due to the crack deflection, with some possible contribution from crack branching or microcracking.

**Key words :** SiC, TiB<sub>2</sub>, Composites, Electrical discharge machinable ceramics

### I. Introduction

Silicon carbide ceramics are one of the most attractive engineering materials under investigation because of their excellent wear and creep resistance. However, low fracture toughness (2.5-4 MPa·m<sup>1/2</sup>) and expensive cost for machining limit their wide applications under stresses or impact.<sup>1)</sup>

Recently, toughening of SiC ceramics has been achieved by using liquid phase sintering and developing duplex microstructure.<sup>2-4)</sup> Several researchers have reported fracture toughness of above 8 MPa·m<sup>1/2</sup> in liquid phase sintered SiC.<sup>5,6)</sup> However, high cost of machining was still remained as a problem in the liquid phase sintered SiC.

Reinforcement of particles with higher hardness, higher elastic modulus, and higher thermal expansion coefficient than SiC is one of the promising methods to increase the toughness. The higher thermal expansion of the reinforcing particles causes radial tensile stress and tangential compressive stress in the SiC matrix.<sup>7)</sup> The stresses make the crack deflection around the reinforcing particles easy, resulting in the increased fracture toughness. Also, addition of material with lower electrical resistivity than SiC makes electrical discharge machining (EDM) of the material possible. EDM is especially effective for machining of complicate shapes, which is impossible or costly by other conventional method. Dispersing particles such as TiB<sub>2</sub><sup>8,9)</sup> and TiC<sup>10,11)</sup> satisfy the above requirements. However, TiB<sub>2</sub> is more promising reinforcing material for electrical discharge machinable SiC ceramics because of the lower electrical resistivity of TiB<sub>2</sub> ( $\approx 10^{-5} \Omega \text{ cm}$ ) than TiC ( $\approx 0.5 \Omega \cdot \text{cm}$ ).<sup>12,13)</sup> Furthermore, TiB<sub>2</sub> has higher hardness and elastic modulus than TiC.

In this study, electrical discharge machinable SiC-TiB<sub>2</sub> composites were prepared by hot-pressing. Their mechanical and electrical properties were determined as a function of TiB<sub>2</sub> content. The feasibility of EDM for SiC-TiB<sub>2</sub> composites was also investigated.

### II. Experimental Procedure

Silicon carbide powder (Betarundum, Ultrafine, Ibiden Co., Ltd, Nagoya, Japan) was mixed in alcohol with 4 wt% phenolic resin, which was equivalent to 1.6 wt% addition of carbon. The slurry was dried and pyrolysed at 650°C for 1 h under argon. The temperature was raised at a rate of 2°C/min. The pyrolysed powders were mixed with 0-60 vol% TiB<sub>2</sub> (grade F, H. C. Starck, Laufenburg, Germany) and 1 wt% aluminum (< 44 μm, Wako Pure Chemical Industries, Ltd., Tokyo, Japan) using polyethylene jar and WC balls. The mixed slurry was then dried, sieved through a 60 mesh screen, and hot-pressed at 1950°C for 40 min with 25 MPa of applied pressure under argon atmosphere.

Densities were measured using the Archimedes method. Theoretical densities were calculated based on the rule of mixtures. The microstructures of hot-pressed samples were observed by optical microscopy and scanning electron microscopy (SEM). The hot-pressed materials were cut into 3×4×25 mm bars and their surfaces and edges were polished with an 800 grit diamond wheel for flexural testing. Four point flexural strength ( $\sigma$ ) was measured at room temperature with outer span of 20 mm and inner span of 8 mm. The fracture toughness ( $K_{IC}$ ) was measured using a Vickers indenter with a load of 49 N.

Electrical resistivity was measured using a 4-point

probe method. EDM was done using wire electrode (Cu wire with the diameter of 0.3 mm) and cutting rates were ranged from 300 to 600 mm/h.

### III. Results and Discussion

Hot-pressing of SiC and SiC-TiB<sub>2</sub> compositions (doped with 1 wt% Al and 1.6 wt% C) containing up to 60 vol% TiB<sub>2</sub> to densities > 99% of theoretical was achieved without difficulty. Table I lists the hot-pressing results. Aluminum additive in the sintering of SiC was known to form grain boundary phases in the form of oxides and also to segregate to grain boundaries to aid densification of SiC.<sup>14</sup> Polycrystalline TiB<sub>2</sub> (doped with 2 wt% carbon) can easily be fabricated to over 99% of theoretical density by hot-pressing at 1700°C and 35 MPa of applied pressure.<sup>15</sup> Such hot-pressing behavior of TiB<sub>2</sub> and the

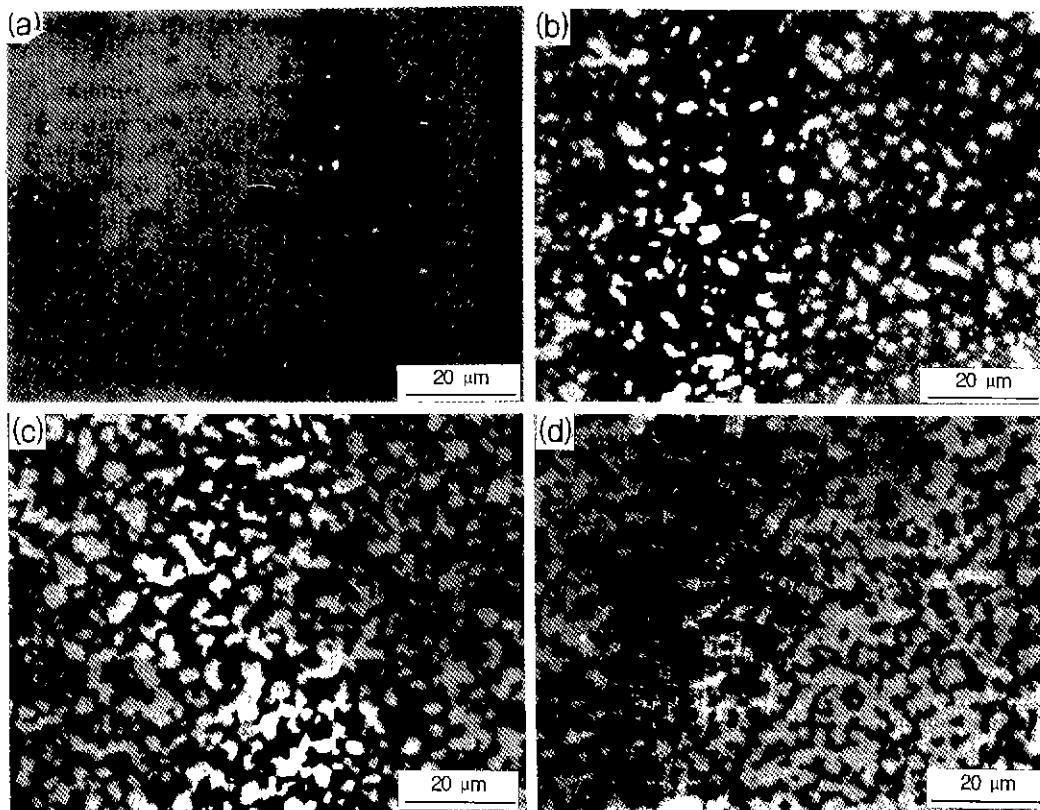
beneficial function of aluminum and carbon in the densification of SiC resulted in the successful densification of the SiC-TiB<sub>2</sub> composites in the present work.

Analysis by X-ray diffraction of the hot-pressed samples revealed  $\beta$ -SiC and TiB<sub>2</sub> as major phases and  $\alpha$ -SiC as a minor phase. Fig. 1 shows optical micrographs of polished surfaces of samples with TiB<sub>2</sub> content of 0-60 vol%. The bright phase is TiB<sub>2</sub>, and the gray matrix is SiC. As shown, the SiC-TiB<sub>2</sub> composites are a two phase particulate composites consisted of randomly distributed TiB<sub>2</sub> particles ranging from 1 to 10  $\mu$ m diameter in the SiC matrix. Most of TiB<sub>2</sub> particles are single grains, but some are clusters of several grains. Fig. 2 shows the fracture surfaces of samples. As shown, grain size of the SiC-TiB<sub>2</sub> composites increases with the content of TiB<sub>2</sub>. It may be due to the increased tendency of TiB<sub>2</sub> clustering with the content of TiB<sub>2</sub>, as evidenced by Fig. 1. The fracture mode was mostly intergranular.

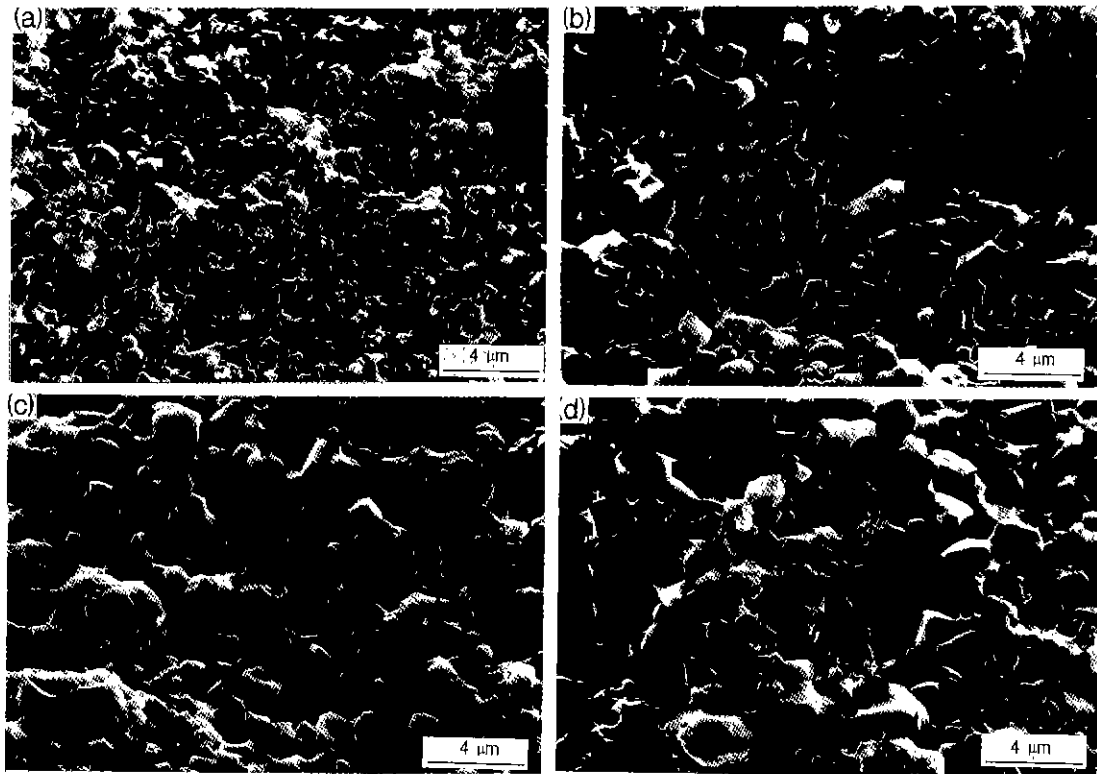
The changes in flexural strength and fracture toughness with the volume fraction of TiB<sub>2</sub> are shown in Fig. 3, where both flexural strength and fracture toughness are seen to increase with the content of TiB<sub>2</sub> up to 40 vol%. It means that TiB<sub>2</sub> addition has a beneficial effect on the mechanical properties of SiC. For the flexural strength, SiC-TiB<sub>2</sub> composites have approximately 20-40% higher values than monolithic SiC. The relative increases in flexural strength and fracture toughness with TiB<sub>2</sub> content are comparable, as one expects from the strength-fracture

**Table I.** Results of Hot-pressing and Electrical Resistivity of Monolithic SiC and SiC-TiB<sub>2</sub> Composites Doped with 1 wt% Al and 1.6 wt% C

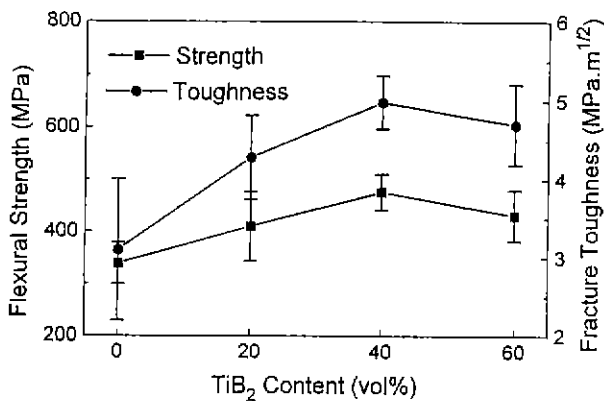
Composition (vol%)	Density		Electrical resistivity (20°C, $\Omega \cdot \text{cm}$ )
	$\text{g/cm}^3$	% of theoretical	
SiC	3.181	99.1	$5.76 \times 10^3$
SiC+20% TiB <sub>2</sub>	3.469	99.9	$3.52 \times 10^1$
SiC+40% TiB <sub>2</sub>	3.734	100	$4.43 \times 10^{-3}$
SiC+60% TiB <sub>2</sub>	3.996	100	$2.51 \times 10^{-3}$



**Fig. 1.** Optical micrographs of polished cross section of SiC and SiC-TiB<sub>2</sub> composites: (a) monolithic SiC, (b) SiC-20 vol% TiB<sub>2</sub>, (c) SiC-40 vol% TiB<sub>2</sub>, and (d) SiC-60 vol% TiB<sub>2</sub>.



**Fig. 2.** Scanning electron micrographs of fracture surfaces of SiC and SiC-TiB<sub>2</sub> composites: (a) monolithic SiC, (b) SiC-20 vol% TiB<sub>2</sub>, (c) SiC-40 vol% TiB<sub>2</sub>, and (d) SiC-60 vol% TiB<sub>2</sub>.



**Fig. 3.** Flexural strength and fracture toughness of SiC and SiC-TiB<sub>2</sub> composites as a function of TiB<sub>2</sub> content.

toughness relationship for Griffith material:

$$\sigma_f = Y K_{IC} c^{-1/2} \quad (1)$$

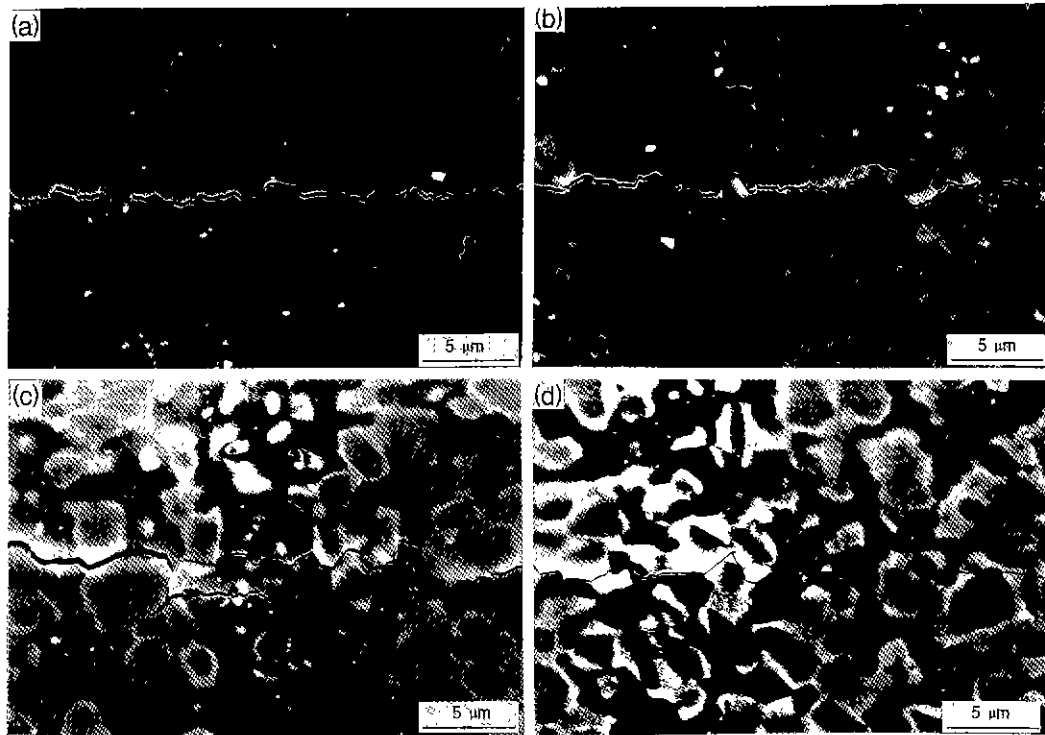
where  $Y$  is a dimensionless constant which depends on the geometry of the loading and crack configuration and  $c$  is the critical flaw size. The observed relative increase in flexural strength with the content of TiB<sub>2</sub> is comparable to the relative increase in fracture toughness, indicating that the toughness is the dominant factor in the improved strength. This behavior is analogous to that of the SiC-TiC composites.<sup>10,16</sup> Lower strength of SiC-60 vol% TiB<sub>2</sub> composites than SiC-40 vol% TiB<sub>2</sub> composites is considered due to the excessive clustering of TiB<sub>2</sub> par-

ticles in SiC-60 vol% TiB<sub>2</sub> composites (Fig. 1). Clustering of TiB<sub>2</sub> particles may increase the effective critical flaw size and result in lower strength of the composites because the large TiB<sub>2</sub> grains can act as a critical flaw.<sup>17</sup>

The fracture toughness of SiC-TiB<sub>2</sub> composites increased with the content of TiB<sub>2</sub> and the maximum was obtained at 40 vol%. The fracture toughness of SiC-40 vol% TiB<sub>2</sub> composites is about 60% higher than that of monolithic SiC. Fig. 4 shows SEM micrographs of cracks induced by a Vickers indenter. The crack front is deflected at TiB<sub>2</sub> particles. It means that the composites have a weak bond between SiC and TiB<sub>2</sub>. The TiB<sub>2</sub> particles have a higher thermal expansion coefficient ( $8.65 \times 10^{-6} \text{ C}^{-1}$ ) than the SiC matrix ( $4.16 \times 10^{-6} \text{ C}^{-1}$ ). The thermal expansion mismatch would result in TiB<sub>2</sub> shrinkage away from the SiC matrix during cooling from the hot-pressing temperature generating a weak SiC-TiB<sub>2</sub> interface. The mismatches between SiC matrix and TiB<sub>2</sub> particle in the linear thermal expansion coefficient ( $\alpha$ ) and elastic modulus ( $E$ ) also result in the generation of the residual stresses in the particles and surrounding matrix during cooling after hot-pressing. The developed residual stress around the particle, radial matrix stress ( $\sigma_{mr}$ ), can be calculated from the following equation:<sup>18</sup>

$$\sigma_{mr} = \frac{(\alpha_p - \alpha_m) \Delta T}{[(1 + \nu_m)/2E_m] + [(1 - 2\nu_p)/E_p]} \quad (2)$$

where  $\nu$  is the Poisson's ratio,  $\Delta T$  is the temperature difference over which stresses are not relieved by a diffusive



**Fig. 4.** Scanning electron micrographs of a crack path induced by a Vickers indenter in SiC and SiC-TiB<sub>2</sub> composites: (a) monolithic SiC, (b) SiC-20 vol% TiB<sub>2</sub>, (c) SiC-40 vol% TiB<sub>2</sub>, and (d) SiC-60 vol% TiB<sub>2</sub>.



**Fig. 5.** Electrical discharge machined SiC-40 vol% TiB<sub>2</sub> composites.

process,<sup>18)</sup> and the subscripts p and m refer to the particle and matrix, respectively.

Taking  $8.65 \times 10^{-6} \text{ C}^{-1}$  and  $4.16 \times 10^{-6} \text{ C}^{-1}$  for  $\alpha_p$  and  $\alpha_m$ ,<sup>7)</sup> 531 GPa and 410 GPa for  $E_p$  and  $E_m$ ,<sup>12)</sup> 0.25 and 0.17 for  $\nu_p$  and  $\nu_m$ ,<sup>19)</sup> and  $1000^\circ\text{C}$  for  $\Delta T$ , the developed radial matrix tensile stress is  $\approx 1900 \text{ MPa}$ . The high tensile stress could be relieved by generating crack branching or microcracking in the vicinity of TiB<sub>2</sub>. The tangential matrix compressive stress ( $\sigma_{mt} = -\sigma_{mr}/2$ ) is  $\approx 950 \text{ MPa}$ . These stress levels will decrease with decreasing the particle radius and increasing the distance from the center of the particles.

A crack will be expected to propagate in a direction parallel to the axis of the local compressive stress and perpendicular to the axis of the local tensile stress in the matrix surrounding the particle. Generally, a crack approaching a particle above or below the crack plane would be deflected toward the radial matrix tensile stress. Observation on the polished surfaces revealed that the cracks were deflected by the TiB<sub>2</sub> particles (Fig. 4). In contrast, monolithic SiC had a fairly planar crack path. Deviations in the crack paths were a result of intergranular fracture in this sample. The amount of crack deflection out of plane (degree of deflection) appeared to increase with increasing TiB<sub>2</sub> content up to 40 vol%. When a crack front interacts with second-phase particles, the crack is deflected. This alters the crack-tip stress intensity and results in improved toughness.<sup>20)</sup> Hence, the higher toughness of SiC-TiB<sub>2</sub> composites compared with monolithic SiC is mainly due to the increased crack deflection around the TiB<sub>2</sub> particles. Crack branching or microcracking caused by high radial tensile stress around TiB<sub>2</sub> particles may also have some contribution to the increased fracture toughness (Fig. 4(c)). The fracture toughness of SiC-60 vol% TiB<sub>2</sub> composites is slightly lower than that of SiC-40 vol% TiB<sub>2</sub> composites. It may be due to the transgranular fracture of large TiB<sub>2</sub> grains (Fig. 4(d)) and the partial loss of composite effect in SiC-60 vol% TiB<sub>2</sub> composites, where the major phase is TiB<sub>2</sub>. Transgranular fracture of large TiB<sub>2</sub> grains reduces the contribution of deflection in toughening and results in

lower fracture toughness. Also, SiC in the TiB<sub>2</sub> matrix cannot act as a reinforcing particles because of lower elastic modulus and thermal expansion coefficient than TiB<sub>2</sub>.

Figure 4 also reveals the existence of a core/rim structure in the TiB<sub>2</sub> grains. Microanalysis using electron probe (EPMA) on the rim area revealed 91.6 at% Ti and 8.4 at% W. In contrast, W-free Ti core was detected. B and C could not be analyzed because of the limited sensitivity of the equipment. W in the rim area is believed to be contaminated during ball milling by WC balls. The above results suggest that the observed core/rim structure might have been developed by the dissolution of nonequilibrium phases in the liquid and a subsequent reprecipitation of equilibrium phases onto undissolved nonequilibrium particles (TiB<sub>2</sub> grains), which constitute cores. It indicates that the grain growth of TiB<sub>2</sub> grains was achieved by solution and reprecipitation mechanism suggested by Rüdiger and Exner.<sup>21</sup> The effect of W on mechanical properties may not be appreciable because TiB<sub>2</sub> grain consisted of core/rim structure behaves as a single grain, as evidenced by Fig. 4 (b) and (c).

The measured electrical resistivities were also summarized in Table 1. SiC is inherently a semiconductor and TiB<sub>2</sub> is inherently a good conductor. The SiC-TiB<sub>2</sub> composites had the electrical resistivity in-between SiC and TiB<sub>2</sub>, as expected. The electrical resistivity of SiC-60 vol% TiB<sub>2</sub> composites is slightly lower than that of SiC-40 vol% TiB<sub>2</sub> composites. It may be due to the formation of continuous skeleton of conducting phase (TiB<sub>2</sub>) in SiC-60 vol% TiB<sub>2</sub> composites. Core/rim structure in Fig. 4 may increase the electrical resistivity of the composites because the electrical resistivity of WC is higher than that of TiB<sub>2</sub>. Hence, use of WC balls are not desirable for the fabrication of EDM SiC-TiB<sub>2</sub> composites. A material which has a resistivity of < 1 cm could be electrical discharge machined.<sup>19</sup> Our result shows that SiC-TiB<sub>2</sub> composites with > 40 vol% TiB<sub>2</sub> could be electrical discharge machined. Fig. 5 shows an example of EDM for SiC-40 vol% TiB<sub>2</sub> composites.

#### IV. Conclusions

Electrical discharge machinable SiC-TiB<sub>2</sub> composites have been fabricated by hot-pressing. Addition of TiB<sub>2</sub> improved the flexural strength and fracture toughness and decreased the electrical resistivity of SiC. Flexural strength and fracture toughness of the SiC-40 vol% TiB<sub>2</sub> composites were 40% and 60%, respectively, higher than those of monolithic SiC. SiC-TiB<sub>2</sub> composites with >40 vol% TiB<sub>2</sub> had a resistivity lower than 10<sup>-2</sup> Ω · cm and could be electrical discharge machined.

Fracture mode of the SiC-TiB<sub>2</sub> composites was mostly intergranular and cracks were deflected by the TiB<sub>2</sub> particles. The toughening was mainly due to the crack deflection with some possible contribution from crack

branching or microcracking.

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